

Abstracts

Low-Noise, Low DC Power Linear Amplifiers (1993 [MCS])

P.K. Ikalainen, L.C. Witkowski and K.R. Varian. "Low-Noise, Low DC Power Linear Amplifiers (1993 [MCS])." 1993 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 93.1 (1993 [MCS]): 159-162.

Single and dual-gate distributed amplifiers designed for standard ion-implanted GaAs FETs and a newly designed Ku-band amplifier were processed using new high dynamic range FET process. State-of-the-art results were achieved in terms of simultaneous linearity, DC power, noise figure, and gain-bandwidth. OIP3/P_{sub dc/} ratios of the amplifiers were in the range 1 to 13.7 with noise figures as low as 3 dB. 8 to 20 dB improvement in second-order linearity has been demonstrated as well.

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